

4-Bit Single-Chip Microcontroller LCD Driver ROM: 2, 4, 6, or 8 K  $\times$  16 bits, RAM: 512  $\times$  4 bits

## **Preliminary**

### Overview

The LC587202A through LC587208A are 4-bit CMOS microcontrollers that integrate ROM, RAM, and an extensive set of peripheral functions around a CPU core that supports low-voltage operation. Memory capacities include 2, 4, 6, or 8 K of 16-bit ROM, 512 × 4 bits of RAM, and a special-purpose RAM for the 8-level stack. Peripheral functions include two 8-bit timers (one of which can be used as an event counter), an 8-bit synchronous serial interface, an alarm signal generator, a remote controller carrier signal generator, and an LCD controller/driver circuit. These microcontrollers provide a powerful set of standby functions for reduced power dissipation.

## **Applications**

- Portable electronic equipment that uses an LCD display (These microcontrollers are particularly well-suited for portable equipment that requires low-power operation for extended battery life.)
- Control and LCD display in portable CD players, timers, and consumer health maintenance equipment
- · Remote controls for CD players, VCRs, and tuners

### **Features**

#### ROM

- LC587208A (8192 × 16 bits)
- LC587206A (6144 × 16 bits)
- LC587204A (4096 × 16 bits)
- LC587202A (2048 × 16 bits)

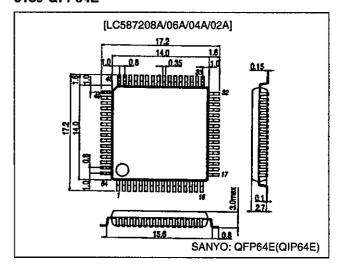
#### **RAM**

- LC587208A (512 × 4 bits)
- LC587206A (512 × 4 bits)
- LC587204A (512 × 4 bits)
- LC587202A (512 × 4 bits)

## **Package Dimensions**

Unit: mm

#### 3159-QFP64E



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#### Instruction cycle times

Except for the table reference instruction, all instructions execute in a single cycle.

Cycle time	Supply voltage	System clock oscillator	Oscillator frequency
667 ns	4.5 to 6.0 V	CF (ceramic) oscillator	6 MHz
1 µs	2.8 to 6.0 V	CF (ceramic) oscillator	4 MHz
4 µs	2.5 to 6.0 V	CF (ceramic) oscillator	1 MHz
10 µs	2.2 to 6.0 V	CF (ceramic) oscillator	400 kHz
122 µs	2.0 to 6.0 V	Crystal oscillator	32.768 kHz

#### **Ports**

Input-only pins

- Port S (4 pins)
- The INT pin (1 pin)

I/O Pins

• Port K (4 pins)

The output circuits are CMOS circuits, and cannot be modified.

• Port M (4 pins)

The output circuits are either CMOS or p-channel circuits, and the type can be selected under program control in single-port units. (The M4 pin is set to its input pin function when timer 2 is used as an event counter.)

• Port SO (4 pins)

The output circuits are either CMOS or n-channel circuits, and the type can be selected under program control in single-port units. The three pins SO1, SO2, and SO3 also function as the serial interface pins. (Two-pin serial interface operation is also supported.)

Port P (4 pins)

The output circuits are either CMOS or p-channel circuits, and the type can be selected under program control in single-port units. Output-only pins

• Port N (4 pins)

The N3 pin also functions as the remote controller carrier output pin, and the N4 pin also functions as the alarm output pin.

#### LCD drive pins

- Common pins (4 pins)
- Segment pins (23 pins)

The segment pin circuits include built-in memory (called "segment memory") that holds the output data. These pins can also be switched in single-pin units in the mask options to function as general-purpose outputs (CMOS, p-channel, or n-channel).

## Wide selection of LCD drive techniques

LCD drive technique	rive technique Number of segments that can be driven	
1/3blas 1/4duty	92 segments	COM1 to COM4
1/3bias 1/3duty	69 segments	COM1 to COM3
1/2bias 1/4duty	92 segments	COM1 to COM4
1/2bias 1/3duty	69 segments	COM1 to COM3
Duplex	46 segments	COM1, COM2
Static	23 segments	COM1

## LCD controller (Hardware functions that facilitate the development of display control software)

Segment PLA (option)

This technique allows the LCD drivers (common 1 through common 4) to be controlled according to user software design, i.e. the relationship between LCD segment control strobe signals and the data. This technique is more difficult for the chip manufacturer, but it allows software design and the LCD panel layout design to be completely independent. Thus it supports highly efficient product development and is a major plus for the user. Furthermore, there is no need for a routine that converts data held in RAM to LCD driver output data.

## Segment decoder

These microcontrollers provide a decoder for 7-segment displays. This circuit also allows binary data to be output without modification for display control of flag areas that display various operating states.

### Strobe decoder

This function groups segments for easier program development and display control.

#### **Timers**

#### Timer 1

- Six-bit prescaler + 8-bit programmable reload timer
   (The prescaler is shared by timer 1, timer 2, and the serial interface.)
- Supports the generation of remote control carrier signals under program control.

#### Timer 2

- Six-bit prescaler + 8-bit programmable timer
   (The prescaler is shared by timer 1, timer 2, and the serial interface.)
- · Can also be used as an event counter.

Base timer (When the 32.768 kHz crystal oscillator option is selected)

• Two frequencies from a set of four base frequencies (either 125 ms and 500 ms, or 100 ms and 250 ms) can be selected as a combination of mask option and program selection to flexibly support end products.

### Standby functions

#### Halt mode

- Instruction execution is stopped in this mode. The oscillator circuits, the timers, the LCD controller and driver circuits, and the serial interface continue to operate. This mode allows unnecessary loops to be avoided and therefore power dissipation can be reduced by the effective use of this mode.
- The halt mode clear (exit) conditions can be set by application programs. The following functions can be used to clear halt mode.
  - Transitions on the INT pin signal (1 factor)
  - Timer 1 (1 factor)
  - Timer 2 (1 factor)
  - Base timer (1 factor)
  - Transitions on either the serial interface pins or the SO4 pin (One or the other of these two factors)
  - Transitions on the S and K port signals as defined by the SSW instruction (8 factors)
  - The reset signal

#### Hold mode

- This is a full standby mode in which the oscillator circuits are stopped.
- The hold mode clear (exit) conditions can be set by application programs. The following functions can be used to clear hold mode.
  - Transitions on the INT pin signal (1 factor)
  - Timer 2 in event counter mode (1 factor)
  - Transitions on either the serial interface pins or the SO4 pin (One or the other of these two factors)
  - Transitions on the S and K port signals as defined by the SSW instruction (8 factors)
  - The reset signal

#### Interrupt function (5 factors with 4 vector addresses)

- Transitions on the INT pin signal (1 factor)
- Timer 1 (1 factor)
- Timer 2 (1 factor)
- Transitions on either the serial interface pins or the SO4 pin (One or the other of these two factors)

## Watchdog timer

A 16-bit counter is used. This circuit supports reset based on a combination of two points the program passes through for flexible application support. This watchdog timer circuit supports the following operating times.

Crystal oscillator used (32.768 kHz, 1 or 2 cycles): Up to 2000 ms (max)

CF oscillator used (1 MHz, 1 cycle):

Up to 65.536 ms (max)

## Subroutine stack

These microcontrollers provide an 8-level stack in special-purpose RAM for subroutines and interrupt handling. Thus data RAM is not required for saving the program counter.

#### Instruction set

These microcontrollers provide 126 easy-to-use instructions, including accumulator manipulation, register to/from memory transfer, arithmetic, logical operation, flag manipulation, and I/O port control instructions, as well as a full set of conditional branch instructions.

### Oscillator circuits (three types)

Single-oscillator specifications: One oscillator, either a CF, RC, or crystal oscillator.

Dual-oscillator specifications: Either a CF and a crystal oscillator, or an RC and a crystal oscillator.

CF (ceramic) oscillator circuit

- · Used for the system clock in fast mode
- 400 kHz to 6 MHz

RC (resistor/capacitor) oscillator circuit

- · Used for the system clock in fast mode
- 400 kHz to 800 kHz
- · Two-terminal oscillator circuit

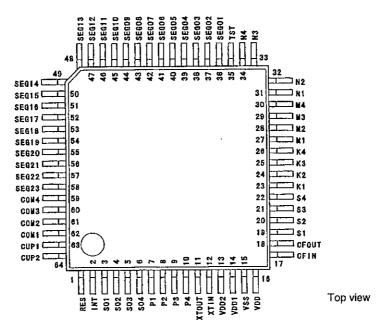
Crystal oscillator circuit

- · Used for the system clock in slow mode
- 32.768, 38.2293, or 65.536 kHz

## Package options

- QIP64E (flat package)
- Chip

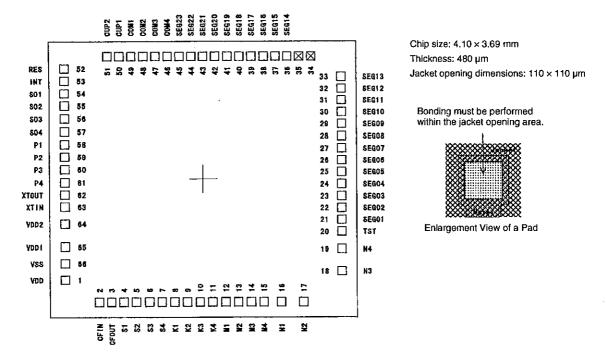
## **Pin Assignment**



Pin 35 (TST) must be connected to VSS during normal operation.
 Consult your Sanyo representative in advance before using solder bath or spray techniques for mounting.

## **Pad Arrangement**

(Applies to the chip version of the product.)



## Pad Coordinates (unit: µm)

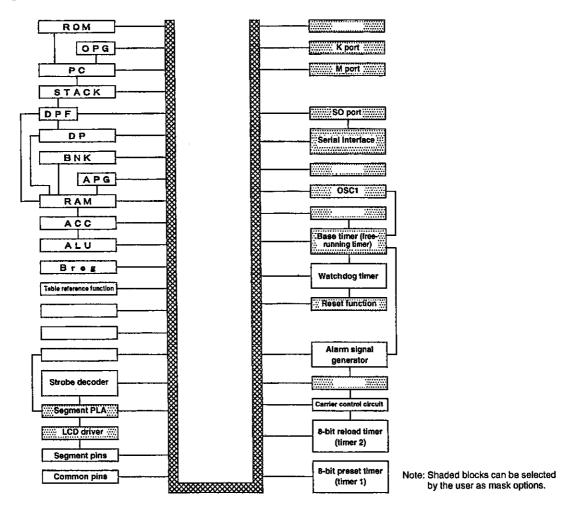
(Applies to the chip version of the product.)

No.	Pad	Х	Υ	No.	Pad	X	Υ
1	DDV	-1854	-1345	34		1452	1650
2	CFIN	-1396	-1650	35	<del></del>	1292	1650
3	CFOUT	-1236	-1650	36	SEG14	1132	1650
4	<b>S</b> 1	-1071	-1650	37	SEG15	972	1650
5	S2	-901	-1650	38	SEG16	812	1650
6	S3	-731	1650	39	SEG17	652	1650
7	S4	-561	-1650	40	SEG18	492	1650
8	K1	-391	-1650	41	SEG19	332	1650
9	K2	-221	-1650	42	SEG20	172	1650
10	КЗ	-51	-1650	43	SEG21	12	1650
11	K4	119	-1650	44	SEG22	-148	1650
12	M1	289	-1650	45	SEG23	-308	1650
13	M2	459	-1650	46	COM4	-468	1650
14	M3	629	-1650	47	СОМЗ	-628	1650
15	M4	799	-1650	48	COM2	-788	1650
16	N1	1034	-1650	49	COM1	-948	1650
17	N2	1333	-1650	50	CUP1	-1108	1650
18	N3	1854	-1234	51	CUP2	-1268	1650
19	N4	1854	-935	52	RES	1854	1488
20	TST	1854	-705	53	INT	-1854	1323
21	SEG01	1854	<b>~</b> 545	54	SO1	-1854	1153
22	SEG02	1854	-385	55	SO2	-1854	983
23	SEG03	1854	~225	56	SO3	1854	813
24	SEG04	1854	-65	57	SO4	-1854	643
25	SEG05	1854	95	58	P1	-1854	473
26	SEG06	1854	255	59	P2	-1854	303
27	SEG07	1854	415	60	P3	-1854	133
28	SEG08	1854	575	61	P4	-1854	-37
29	SEG09	1854	735	62	XTOUT	-1854	-202
30	SEG10	1854	895	63	XTIN	-1854	-362
31	SEG11	1854	1055	64	VDD2	-1854	-594
32	SEG12	1854	1215	65	VDD1	-1854	898
33	SEG13	1854	1375	66	VSS	-1854	-1122

<sup>.</sup> Pad 20 must be connected to VSS.

<sup>•</sup> Pads 34 and 35 must be left open.

## **System Block Diagram**



## Mask options overview

Mask options are provided to allow the microcontroller hardware functions to closely match the specifications of the end product. The user can select any combination of options desired. In addition, these microcontroller also provide, as a mask option, a segment PLA function that can set up a correspondence, in single-segment units, between the operation of independently developed software and the actual LCD segments.

#### Oscillator Circuit Options

- Oscillator selection: Selects oscillator specifications appropriate for the application.
  - 1: CF, 2: EXT, 3: RC, 4: Crystal, 5: CF & crystal, 6: EXT & crystal, 7 RC & crystal
- CF/EXT frequency: Selects the frequency of the CF (ceramic) or external oscillator.
  - 1: 400 kHz/10 μs, 2: 800 kHz/5 μs, 3: 2 MHz/2 μs, 4: 4 MHz/1 μs, 5: 6 MHz/0.7μs
- RC frequency: Selects the frequency of the RC (resistor/capacitor) oscillator.
  - 1: 400 kHz/10 μs, 2: 800 kHz/5 μs
- Xtal selection: Selects the frequency of the crystal oscillator.
  - 1: 32 kHz/122 μs, 2: 38 kHz/105 μs, 3: 65 kHz/61 μs
- Crystal oscillator specification: Selects the Rd and Cd used with the crystal oscillator.
  - 1: Internal Rd and Cd used, 2: Internal Rd and Cd unused

## LCD Controller/Driver Options

- LCD driver: Selects the LCD driver/controller operating mode appropriate for the drive technique used by the LCD panel used.
  - 1: Static, 2: Duplex, 3: 1/2B-1/3D, 4: 1/2B-1/4D, 5: 1/3B-1/3D, 6: 1/3B-1/4D, 7 Unused
- LCD frequency: Selects the drive frequency (frame frequency) appropriate for the LCD panel used.
  - 1: Slow, 2: Typ, 3: Fast

## **Base Timer Options**

- Base timer overflow signal: Selects the base timer basic frequency.
  - 1: DIVIN divided by 8192 or 32768, 2: DIVIN divided by 4096 or 16384

#### Serial Interface Options

- SIO counter internal clock speed: Selects the frequency of the internal clock used by the serial interface.
  - 1: 1 machine cycle, 2: 2 machine cycles, 3: 4 machine cycles

#### **INT Pin Options**

- INT pin resistor: Selects the type of INT pin input circuit appropriate for the application
  - 1: Pulled down, 2: Pulled up, 3: Open
- INT pin interrupt edge: Selects the input level at which the INT external interrupt pin operates.
  - 1: Falling edge (high to low), 2: Rising edge (low to high)
- · INT pin hold transistor: Selects whether or not the level hold function built into the INT pin circuit is used.
  - 1: Low/high level hold transistor used, 2: Low/high level hold transistor unused

#### Reset Options

- RESET pin resistor: Selects the type of RES pin input circuit appropriate for the application
  - 1: Pulled down (high resistance), 2 Pulled up (low resistance), 3: Open (high resistance), 4: Open (low resistance)
- Internal reset: Selects whether or not the internal reset circuit should be used in conjunction with the external reset function.
  - 1: Used, 2: Unused

#### Port Internal Resistor Options

- Resistor connection selection: Selects the programmable resistors and the level hold functions that are built into the input ports.
  - 1. Pull-down resistor, 2: Pull-up resistor

Port Built-in Level Hold Function Options (Selected in 4-bit units): These depend on which of the above-described options were selected.

- Port S hold transistor: Selects whether or not the port S level hold function is used.
  - 1: Low/high level hold transistors used, 2: Low/high level hold transistors unused
- Port K hold transistors: Selects whether or not the port K level hold function is used.
  - 1: Low/high level hold transistors used, 2: Low/high level hold transistors unused
- Port M hold transistors: Selects whether or not the port M level hold function is used.
  - 1: Low/high level hold transistors used, 2: Low/high level hold transistors unused
- Port P hold transistors: Selects whether or not the port P level hold function is used.
  - 1: Low/high level hold transistors used, 2: Low/high level hold transistors unused
- Port SO hold transistors: Selects whether or not the port SO level hold function is used.
  - 1: Low/high level hold transistors used, 2: Low/high level hold transistors unused

## Port N Options

- N1 pin output type: Selects the type of the port N1 output circuit.
  - 1: CMOS type, 2: N-channel type
- N2 pin output type: Selects the type of the port N2 output circuit.
  - 1: CMOS type, 2: N-channel type
- N3 pin output type: Selects the type of the port N3 output circuit.
  - 1: CMOS type, 2: N-channel type
- N4 pin output type: Selects the type of the port N4 output circuit.
  - 1: CMOS type, 2: N-channel type
- Port N initial output state: Selects the output levels for port N (N1 through N4) when the reset signal is applied.
  - 1: High level or off, 2: Low level

## **Pin Functions**

Pin	1/0	Function	State during a reset
vss	_	Ground (–)	
VDD	_	Power supply (+)	
		LCD power supply connections	
		The external handling of these pins differs depending on the LCD drive bias technique used.	
VDD1 VDD2		LCD drive blas	
		VDD2 vSS c1 c2	
		LCD drive pins     The external handling of these pins differs depending on the LCD drive bias technique used.	
CUP1 CUP2	_ _ _	LCD drive bias   Unused   1/1   1/2   1/3     1/2   1/3	·
CFIN CFOUT	Input Output	OSC1 (fast mode) oscillator element connections     CF specifications: 400 kHz to 6 MHz     RC specifications: 400 kHz to 800 kHz     EXT specifications: 200 kHz to 4 MHz	
XTIN XTOUT	Input Output	OSC2 (slow mode) oscillator element connections     Xtal: 32, 38, or 65 kHz	
INT	Input	<ul> <li>1-bit input</li> <li>External Interrupt input</li> <li>The input circuit type and the interrupt level are set in the mask options. (Pulled up, pulled down, or open)</li> <li>(Rising edge or falling edge)</li> <li>A level hold function, which is designed to prevent input floating states from occurring, is also available as an option.</li> </ul>	Interrupt reception: disabled     Level hold function: operational
S1 S2 S3 S4	Input Input Input Input	<ul> <li>4-bit input port</li> <li>Pull-up and pull-down resistors, which can be enabled or disabled under program control in a single port unit, are built in.</li> <li>Input signal transition detection circuits and chattering exclusion circuits, which can be enabled or disabled under program control in 1-bit units, are built in.</li> <li>The chattering exclusion time differs depending on the oscillator specifications. When a 32.768 kHz crystal oscillator is used the time will be 1.95 or 7.8 ms.</li> <li>A level hold function, which is designed to prevent input floating states from occurring on these pins, is also available as an option.</li> </ul>	Pull-down or pull-up resistors: enabled (After the reset is cleared: disabled) Level hold function: operation disabled (After the reset is cleared: operation starts)
K1 K2 K3 K4	1/0 1/0 1/0 1/0	4-bit I/O port     Pull-up and pull-down resistors, which can be enabled or disabled under program control in a single port unit, are built in.     Input signal transition detection circuits and chattering exclusion circuits, which can be enabled or disabled under program control in a single port unit, are built in.     The chattering exclusion time differs depending on the oscillator specifications.     When a 32.768 kHz crystal oscillator is used the time will be 1.95 or 7.8 ms.     Output circuit type: CMOS     A level hold function, which is designed to prevent input floating states from occurring on these pins, is also available as an option.	Input mode Pull-down or pull-up resistors: enabled (After the reset is cleared: disabled) Level hold function: operation disabled (After the reset is cleared: operation starts) Output latch data: high

#### Continued from preceding page.

Pin	I/O	Function	State during a reset
SO1 SO2 SO3 SO4	1/0 1/0 1/0	<ul> <li>4-bit I/O port (also used for the serial interface)</li> <li>SO1: Serial interface input</li> <li>SO2: Serial interface output</li> <li>SO3: Serial interface clock</li> <li>The serial interface can also be used as a 2-wire interface.</li> <li>When the serial interface function is not used, the SO4 pin can be used to clear halt mode or as an interrupt pin.</li> <li>Pull-up and pull-down resistors, which can be enabled or disabled under program control in a single port unit, are built in.</li> <li>The output circuit type can be switched under program control in a single port unit. (CMOS/n-channel)</li> <li>A level hold function, which is designed to prevent input floating states from occurring on these pins, is also available as an option.</li> </ul>	Input mode Pull-down or pull-up resistors: enabled (After the reset is cleared: disabled) Level hold function: operation disabled (After the reset is cleared: operation starts)  4-bit parallel mode Output latch data: high
M1 M2 M3 M4	I/O I/O I/O I/O	<ul> <li>4-bit I/O port</li> <li>Pull-up and pull-down resistors, which can be enabled or disabled under program control in a single port unit, are built in.</li> <li>The output circuit type can be switched under program control in a single port unit. (CMOS/n-channel)</li> <li>The M4 pin functions as a clock input when timer 2 is operated in event counter mode.</li> <li>A level hold function, which is designed to prevent input floating states from occurring on these pins, is also available as an option.</li> </ul>	Input mode Pull-down or pull-up resistors: enabled (After the reset is cleared: disabled) Level hold function: operation disabled (After the reset is cleared: operation starts) Output latch data: high
P1 P2 P3 P4	1/O 1/O 1/O 1/O	4-bit I/O port     Pull-up and pull-down resistors, which can be enabled or disabled under program control in a single port unit, are built in.     The output circuit type can be switched under program control in a single port unit. (CMOS/n-channel)     A level hold function, which is designed to prevent input floating states from occurring on these pins, is also available as an option.	Input mode Pull-down or pull-up resistors: enabled (After the reset is cleared: disabled) Level hold function: operation disabled (After the reset is cleared: operation starts) Output latch data: high
N1 N2 N3 N4	Output Output Output Output	4-bit output port     The output circuit type can be switched under program control in 1-bit units. (CMOS/n-channel)     This port handles medium-level voltages when the n-channel open-drain output circuit type is selected.     N3 is the remote controller carrier signal output pin.     N4 is the alarm pulse signal output pin.	,
SEG1 to SEG23	Output	LCD panel segment drive pins     Six drive techniques are supported.     These pins can be used as general-purpose outputs (either CMOS, p-channel, or n-channel) by specifying mask options.     Any combination of LCD drive and general-purpose output pins can be set up.	The states of those pine set up as general-purpose
COM1 COM2 COM3 COM4	Output Output Output Output	LCD panel common plate drive pins     One of four pins COM1 to COM4 is selected according to the LCD drive duty technique used.     The LCD drive frequency (frame frequency) is determined by the mask option.	depending on the oscillator specifications and other
RES	Input	<ul> <li>Microcontroller reset input         Applications must apply the reset signal level for at least 200 µs.     </li> <li>The input circuit and the reset level are specified as mask options.</li> </ul>	·
TST	Input	Test input This pin must be tied to the VSS level (the minus side of the power supply).	

# **Specifications**

# Absolute Maximum Ratings at Ta = 25°C, $V_{SS} = 0$ V

Damanata	0			Ratings		Limia
Parameter	Symbol	Conditions and applicable pins		typ	max	Unit
· · · · · · · · · · · · · · · · · · ·	V <sub>DD</sub>		-0.3		+7.0	٧
Maximum supply voltage	V <sub>DD</sub> 1		0.3		V <sub>DD</sub>	٧
	V <sub>DD</sub> 2		-0.3		$V_{DD}$	٧
	V <sub>1</sub> 1	Allowable levels in the specified circuit. XTIN, CFIN	Voltages up to t	ne generated vo	ltage are allowed.	
Maximum input voltage	V <sub>I</sub> 2	S1 to 4, K1 to 4, P1 to 4, SO1 to 4, RES, INT, TST (With the K, P, M, and SO ports in input mode)	-0.3		V <sub>DO</sub> + 0.3	٧
	V <sub>O</sub> 1	Allowable levels in the specified circuit. XTOUT, CFOUT	Voltages up to t	ne generated vo	ltage are allowed.	
Maximum output voltage	V <sub>O</sub> 2	K1 to 4, P1 to 4, SO1 to 4, N1 to 4, CUP1, CUP2, Seg1 to 23, COM1 to 4 (With the K, P, M, and SO ports in output mode)		1	V <sub>DD</sub> + 0.3	٧
	V <sub>O</sub> 3	With the open-drain specifications N1 o 4 (Nch)	-0.3		+16	٧
	101		0		+10	mA
	102	Per pln. K1 to 4, P1 to 4, M1 to 4, SO1 to 4	-10		0	mA
Die entert entert	103	i	0		5	mΑ
Pin output current	104		<b>-</b> 5		0	mA
	ΣΙ <sub>Ο</sub> 1	Total current for all pins: K1 to 4, P1 to 4, M1 to 4, SO1 to 4			40	mA
	Σl <sub>O</sub> 2	N1 to 4, Seg1 to 35	-40			mA
Allowable power dissipation	Pd max	QFP64E(QIP64E) flat package			300	mW
Operating temperature	Topr		-30		+70	°C
Storage temperature	Tstg		55		+125	°C

# Allowable Operating Ranges at $Ta = -30 \text{ to } +70^{\circ}\text{C}$ , $V_{SS} = 0 \text{ V}$

-		A 114		Ratings		Unit
Parameter	Symbol	/mbol Conditions and applicable pins		typ	max	Onit
		LCD unused specifications: V <sub>DD</sub> 1 = V <sub>DD</sub> 2 = V <sub>DD</sub>	2.0		6.0	V
	·	Static drive specifications: V <sub>DD</sub> 1 = V <sub>DD</sub> 2 = V <sub>DD</sub>	2.0		6.0	V
Supply voltage	VDD	1/2 bias specifications: V <sub>DD</sub> 1 = V <sub>DD</sub> 2 = 1/2V <sub>DD</sub>	2.8		6.0	V
		1/3 bias specifications: V <sub>DD</sub> 1 = 2 × 1/3V <sub>DD</sub> , V <sub>DD</sub> 2 = 1/3V <sub>DD</sub>	2.8		6.0	V
Memory retention supply voltage	V <sub>HD</sub>	Voltages at which the RAM and register contents are retained*	2.0		V <sub>DD</sub>	V
High-level input voltage	V <sub>IH</sub> 1	S1 to 4, K1 to 4, P1 to 4, M1 to 4, SO1 to 4, INT (With the K, P, M, and SO ports in input mode)	0.7 V <sub>DD</sub>		V <sub>DD</sub>	٧
Low-level input voltage	V <sub>IL</sub> 1	S1 to 4, K1 to 4, P1 to 4, M1 to 4, SO1 to 4, INT (With the K, P, M, and SO ports in input mode)	0		0.3 V <sub>DD</sub>	ν
High-level Input voltage	V <sub>IH</sub> 2	RES	0.75 V <sub>DD</sub>		V <sub>DD</sub>	V
Low-level input voltage	V <sub>IL</sub> 2	RES	0		0.25 V <sub>DD</sub>	V
High-level Input voltage	V <sub>IH</sub> 3	CFIN	0.75 V <sub>DD</sub>		V <sub>DD</sub>	V
Low-level input voltage	V <sub>IL</sub> 3	CFIN	0		0.25 V <sub>DD</sub>	V
Operating frequency 1	fopg1	V <sub>DD</sub> = 2.0 V to 6.0 V, XTIN/XOUT, 32 kHz Crystal oscillator	32		33	kHz
Operating frequency 2	fopg2	V <sub>DD</sub> = 2.2 V to 6.0 V, XTIN/XOUT, 38 kHz Crystal oscillator	37		39	kHz
Operating frequency 3	fopg3	V <sub>DD</sub> = 2.2 V to 6.0 V, XTIN/XOUT, 65 kHz Crystal oscillator	60		70	kHz
Operating frequency 4	fopg4	V <sub>DD</sub> = 2.2 V to 6.0 V CFIN, CFOUT CF specifications	390		810	kHz
Operating frequency 5	fopg5	V <sub>DD</sub> = 2.5 V to 6.0 V CFIN, CFOUT CF specifications	390		1200	kHz
Operating frequency 6	fopg6	V <sub>DD</sub> = 2.8 V to 6.0 V CFIN, CFOUT CF specifications	390		4200	kHz
Operating frequency 7	fopg7	V <sub>DD</sub> = 4.5 V to 6.0 V CFIN, CFOUT CF specifications	390		6000	kHz
Operating frequency 8	fopg8	V <sub>DD</sub> = 4.5 V to 6.0 V CFIN, CFOUT RC specifications	400		800	kHz
Operating frequency 9	fopg9	V <sub>DD</sub> = 3.0 V to 6.0 V CFIN, CFOUT EXT specifications	190		4000	kHz
Operating frequency 10	fopg10	V <sub>DD</sub> = 3.0 V to 6.0 V Pins SO1 and SO3 (in serial interface mode) Rising and falling edges on the input signal and clock waveform must be ≤ 10 µs	DC		200	kHz

Note \*: The state where the CF/RC and crystal oscillators are completely stopped, and all internal circuits completely stopped.

# Electrical Characteristics at Ta = -30 to +70 °C, $V_{DD} = 2.5$ to 3.2 V, $V_{SS} = 0$ V

	Cb.al	Conditions and applicable pins		Ratings		Unit
w-level output voltage gh-level output voltage w-level output voltage utput off leakage current egment Port Output Impedance MOS output port mode] gh-level output voltage ow-level output voltage -channel open-drain output po gh-level output voltage	Symbol	Conditions and applicable plus	min	typ	max	OTIL
	R <sub>IN</sub> 1 A	V <sub>IN</sub> = 0.2 V <sub>DD</sub> , Low level hold transistor*	60	300	1200	kΩ
	R <sub>IN</sub> 1 B	Pull-down resistor*	30	150	500	kΩ
	R <sub>IN</sub> 1 C	V <sub>IN</sub> = 0.8 V <sub>DD</sub> , High level hold transistor*	60	300	1200	kΩ
	R <sub>IN</sub> 1 D	V <sub>IN</sub> = V <sub>SS</sub> , Pull-up resistor*	30	150	500	kΩ
	R <sub>IN</sub> 2 A	V <sub>IN</sub> = 0.2 V <sub>DD</sub> , INT pin low level hold transistor	60	300	1200	kΩ
input resistance	R <sub>IN</sub> 2 B	V <sub>IN</sub> = V <sub>DD</sub> , INT pin pull-down resistor	300	1500	5000	kΩ
	R <sub>IN</sub> 2 C	V <sub>IN</sub> = 0.8 V <sub>DD</sub> , INT pin high level hold transistor	60	300	1200	kΩ
	R <sub>IN</sub> 2 D	V <sub>IN</sub> = V <sub>SS</sub> , INT pin pull-up resistor	300	1500	5000	kΩ
	R <sub>IN</sub> 3	V <sub>IN</sub> = V <sub>DD</sub> , RES pin pull-down resistor	10	30	50	kΩ
	R <sub>IN</sub> 4	V <sub>IN</sub> = V <sub>SS</sub> , RES pin pull-up resistor	10	30	50	kΩ
	R <sub>IN</sub> 5	V <sub>IN</sub> = V <sub>DD</sub> , TST pin pull-down resistor	10	30	50	kΩ
High-level output voltage	V <sub>OH</sub> 1	I <sub>OH</sub> = -500 μA, N1 to 4	V <sub>DD</sub> – 0.5			٧
Low-level output voltage	V <sub>OL</sub> 1	I <sub>OL</sub> = 1.0 mA, N1 to 4			0.5	_ V
High-level output voltage	V <sub>OH</sub> 2	I <sub>OH</sub> = -400 μA, K1 to 4, P1 to 4, M1 to 4, SO1 to 4 (With the K, P, M, and SO ports in output mode)	V <sub>DD</sub> - 0.5			٧
Low-level output voltage	Vol2	I <sub>OL</sub> = 400 μA, K1 to 4, P1 to 4, M1 to 4, SO1 to 4 (With the K, P, M, and SO ports in output mode)			0.5	٧
Output off leakage current	I OFF1	V <sub>OH</sub> = 10.5 V, N1 to 4 (Open specifications)			1.0	μА
Segment Port Output Impedance						
[CMOS output port mode]						
High-level output voltage	V <sub>OH</sub> 3	I <sub>OH</sub> = -100 μA, Seg 1 to 23	V <sub>DD</sub> - 0.5			V
Low-level output voltage	V <sub>OL</sub> 3	I <sub>OL</sub> = 100 μA, Seg 1 to 23			0.5	V
[P-channel open-drain output po	rt mode]					
High-level output voltage	V <sub>OH</sub> 3	I <sub>OH</sub> = -100 μA, Seg 1 to 23	V <sub>DD</sub> - 0.5			٧
Output off leakage current	I OFF	V <sub>OL</sub> = V <sub>SS</sub> , Seg 1 to 23			1.0	μA
[N-channel open-drain output po	ort mode]					
Low-level output voltage	V <sub>OL</sub> 3	I <sub>OL</sub> = 100 μA, Seg 1 to 23			0.5	٧
Output off leakage current	OFF	V <sub>OH</sub> = V <sub>DD</sub> , Seg 1 to 23			1.0	μΑ
[Static drive]						
High-level output voltage	V <sub>OH</sub> 4	I <sub>OH</sub> = -20 μA, Seg 1 to 23	V <sub>DD</sub> - 0.2			٧
Low-level output voltage	V <sub>OL</sub> 4	I <sub>OL</sub> = 20 μA, Seg 1 to 23			0.2	V
High-level output voltage	V <sub>OH</sub> 5	I <sub>OH</sub> = -100 μA, COM1	V <sub>DD</sub> - 0.2			٧
Low-level output voltage	V <sub>OL</sub> 5	I <sub>OL</sub> = 100 μA, COM1			0.2	٧
					******	

Note \*: The 20 pins S1 to S4, K1 to K4, P1 to P4, M1 to M4, and SO1 to SO4.

# Electrical Characteristics at Ta = –30 to +70 $^{\circ}C,\,V_{DD}$ = 3.0 to 4.5 V, $V_{SS}$ = 0 V

Parameter	Symbol	Conditions and applicable pins		Ratings		Unit
· alameter	Symbol	- January and approximation print		typ	max	Unit
	R <sub>IN</sub> 1 A	V <sub>IN</sub> = 0.2 V <sub>DD</sub> , Low level hold transistor*	35	200	800	kΩ
	R <sub>IN</sub> 1 B	Pull-down resistor*	15	80	300	kΩ
igh-level output voltage ow-level output voltage igh-level output voltage igh-level output voltage ow-level output voltage ow-level output voltage output off leakage current egment Port Output impedances cMOS output port mode] igh-level output voltage ow-level output voltage ow-level output voltage output off leakage current i-channel open-drain output port i ow-level output voltage output off leakage current static drive] igh-level output voltage ow-level output voltage igh-level output voltage ow-level output voltage igh-level output voltage	R <sub>IN</sub> 1 C	V <sub>IN</sub> = 0.8 V <sub>DD</sub> , High level hold transistor*	35	200	800	kΩ
	R <sub>IN</sub> 1 D	V <sub>IN</sub> = V <sub>SS</sub> , Pull-up resistor*	15	80	300	kΩ
Inout resistance	R <sub>IN</sub> 2 A	V <sub>IN</sub> = 0.2 V <sub>DD</sub> , INT pin low level hold transistor	35	200	800	kΩ
	R <sub>IN</sub> 2 B	V <sub>IN</sub> = V <sub>DD</sub> , INT pin pull-down resistor	150	800	3000	kΩ
	R <sub>IN</sub> 2 C	$V_{IN} = 0.8 V_{DD}$ , INT pln high level hold transistor	35	200	800	kΩ
	R <sub>IN</sub> 2 D	V <sub>IN</sub> = V <sub>SS</sub> , INT pin pull-up resistor	150	800	3000	kΩ
	R <sub>IN</sub> 3	V <sub>IN</sub> = V <sub>DD</sub> , RES pin pull-down resistor	10	30	50	kΩ
	R <sub>IN</sub> 4	V <sub>IN</sub> = V <sub>SS</sub> , RES pin pull-up resistor	10	30	50	kΩ
	R <sub>IN</sub> 5	V <sub>IN</sub> = V <sub>DD</sub> , TST pin pull-down resistor	10	30	50	kΩ
High-level output voltage	V <sub>OH</sub> 1	I <sub>OH</sub> = -1.0 mA, N1 to 4	V <sub>DD</sub> - 0.5			V
Low-level output voltage	V <sub>OL</sub> 1	I <sub>OL</sub> = 2.0 mA, N1 to 4			0.5	٧
High-level output voltage	V <sub>OH</sub> 2	I <sub>OH</sub> = -500 μA, K1 to 4, P1 to 4, M1 to 4, SO1 to 4 (With the K, P, M, and SO ports in output mode)	V <sub>DD</sub> - 0.5			٧
Low-level output voltage	V <sub>OL</sub> 2	I <sub>OL</sub> = 500 μA, K1 to 4, P1 to 4, M1 to 4, SO1 to 4 (With the K, P, M, and SO ports in output mode)			0.5	٧
Output off leakage current	I OFFI	V <sub>OH</sub> = 10.5 V, N1 to 4 (Open specifications)			1.0	μА
Segment Port Output Impedances			<u></u>		I	·
[CMOS output port mode]						
High-level output voltage	V <sub>OH</sub> 3	I <sub>OH</sub> = −300 μA, Seg 1 to 23	V <sub>DD</sub> – 0.5			٧
Low-level output voltage	V <sub>OL</sub> 3	I <sub>OL</sub> = 300 μA, Seg 1 to 23		· · · · · · · · · · · · · · · · · · ·	0.5	V
[P-channel open-drain output port m	node]				<del></del>	
High-level output voltage	V <sub>OH</sub> 3	I <sub>OH</sub> = -300 μA, Seg 1 to 23	V <sub>DD</sub> - 0.5			V
Output off leakage current	OFF	V <sub>OL</sub> = V <sub>SS</sub> , Seg 1 to 23			1.0	μA
[N-channel open-drain output port m	node]					
Low-level output voltage	V <sub>OL</sub> 3	I <sub>OL</sub> = 300 μA, Seg 1 to 23			0.5	٧
Output off leakage current	OFF	V <sub>OH</sub> = V <sub>DD</sub> , Seg 1 to 23			1.0	μA
[Static drive]						
High-level output voltage	V <sub>OH</sub> 4	I <sub>OH</sub> = -20 μA, Seg 1 to 23	V <sub>DD</sub> – 0.2			٧
Low-level output voltage	V <sub>OL</sub> 4	I <sub>OL</sub> = 20 μA, Seg 1 to 23			0.2	٧
High-level output voltage	V <sub>OH</sub> 5	I <sub>OH</sub> = -100 μA, COM1	V <sub>DD</sub> = 0.2			V
Low-level output voltage	V <sub>OL</sub> 5	I <sub>OL</sub> = 100 μA, COM1			0.2	V
[1/2 blas drive]						
High-level output voltage	V <sub>OH</sub> 4	I <sub>OH</sub> = -20 μA, Seg 1 to 23	V <sub>DD</sub> – 0.2			٧
Low-level output voltage	V <sub>OL</sub> 4	I <sub>OL</sub> = 20 μA, Seg 1 to 23			0.2	٧
High-level output voltage	V <sub>OH</sub> 5	I <sub>OH</sub> = -100 μA, COM1 to 4	V <sub>DD</sub> - 0.2			٧
Output middle-level voltage	V <sub>OM</sub>	I <sub>OH</sub> = -100 μA, COM1 to 4	V <sub>DD</sub> /2 - 0.2		V <sub>DD</sub> /2 + 0.2	٧
	· OW	I <sub>OL</sub> = 100 μA, COM1 to 4	-0.2		+0.2	٧
Low-level output voltage	V <sub>OL</sub> 5	l <sub>OL</sub> = 100 μA, COM1 to 4			0.2	٧
[1/3 bias drive]						
High-level output voltage	V <sub>OH</sub> 4	I <sub>OH</sub> = -20 μA, Seg1 to 23	V <sub>DD</sub> + 0.2			٧
Output middle-level voltage	V <sub>OM</sub> 1-1	l <sub>OH</sub> = -20 μA, Seg1 to 23	2V <sub>DO</sub> /3 - 0.2		2V <sub>DD</sub> /3 + 0.2	٧
	V <sub>OM</sub> 1-2	I <sub>OL</sub> = 20 μA, Seg1 to 23	V <sub>DD</sub> /3 – 0.2		$V_{DD}/3 + 0.2$	٧
Low-level output voltage	V <sub>OL</sub> 4	i <sub>OL</sub> = 20 μA, Seg 1 to 23			0.2	٧
High-level output voltage	V <sub>OH</sub> 6	i <sub>OH</sub> = -100 μA, COM1 to 4	V <sub>DD</sub> ~ 0.2			٧
Output middle-level voltage	V <sub>OM</sub> 2-1	l <sub>OH</sub> = -100 μA, COM1 to 4	2V <sub>DD</sub> /3 - 0.2		2V <sub>00</sub> /3+0.2	V
	V <sub>OM</sub> 2-2	I <sub>OL</sub> = 100 μA, COM1 to 4	V <sub>DD</sub> /3 – 0.2		V <sub>DD</sub> /3 + 0.2	٧
Low-level output voltage	V <sub>QL</sub> 6	l <sub>OL</sub> = 100 μA, COM1 to 4			0.2	٧

Note \*: The 20 pins S1 to S4, K1 to K4, P1 to P4, M1 to M4, and SO1 to SO4.

#### Continued from preceding page.

D	Symbol Conditions		and applicable pins	Ratings			Unit
Parameter	Symbol _	Conditions	and applicable pins	min	typ	max	
2 l . l l	ILEK1	$V_{DD} = 3.0 \text{ V}$ , $Ta = 25^{\circ}\text{C}$			0.2	1.0	μA
Supply leakage current	ILEK2	$V_{DD} = 3.0 \text{ V}$ , $Ta = 50^{\circ}\text{C}$			1.0	5.0	μA
Input leakage cuπent	I OFF	V <sub>IN</sub> = V <sub>SS</sub>   (With the I	V, S1 to 4, K1 to 4, P1 to 4, M1 to 4, INT, RES With the open specifications or the INT and RES pins.)	-1.0		1.0	μA Aų
Output voltage 1	V <sub>DD</sub> 1-1		0, 1 μF, V <sub>DD</sub> 1 = V <sub>DD</sub> 2, 1/2Bias,	1.3	1.5	1.7	٧
	I <sub>DD</sub>  1-1	V <sub>DD</sub> = 3.0 V, Ta = 25°C	Crystal oscillator specifications Crystal: 32 kHz (Cd and Rd built in)		7	15	μΑ
Supply current 1	I <sub>DD</sub>  1-2	V <sub>DD</sub> = 3.0 V, Ta = 50°C	Cg = 11 pF, Cl = 31 kΩ Halt mode, LCD = 1/3bias			20	μА
	∥ <sub>DD</sub>  2-1	V <sub>DD</sub> = 3.0 V, Ta = 25°C	CF oscillator specifications CF: 455 kHz		100	150	μΑ
Supply current 2	I <sub>DD</sub>  2-2	V <sub>DD</sub> = 3.0 V, Ta = 50°C	Ccg = Ccd = 220 pF Halt mode, LCD = 1/3 blas			200	μА
	I <sub>DD</sub>  3-1	V <sub>DD</sub> = 3.0 V, Ta = 25°C	CF oscillator specifications CF: 1000 kHz		150	200	μА
Supply current 3	I <sub>DD</sub>  3-2	V <sub>DD</sub> = 3.0 V, Ta = 50°C	Ccg = Ccd = 100 pF Halt mode, LCD = 1/3 blas			300	μА
-	I <sub>DD</sub>  4-1	V <sub>DD</sub> = 3.0 V, Ta = 25°C	CF oscillator specifications CF: 4000 kHz		160	220	μA
Supply current 4	I <sub>DD</sub>  4-2	V <sub>DD</sub> = 3.0 V, Ta = 50°C	Ccg = Ccd = 33 pF Halt mode, LCD = 1/3 bias			330	μA
Oscillator startup voltage	V <sub>STT</sub> 1	Tstt ≤ 5 s				2.2	V
Oscillator hold voltage	V <sub>HOLD</sub>		Crystal oscillator specifications Crystal: 32 kHz (Cd and Rd built in)	2.0		6.0	V
Oscillator startup time	T <sub>STT</sub>	V <sub>DD</sub> = 2.2 V	$Ciystal. 32 KHZ (Collain Ru built iii)  Cig = 11 \text{ pF, } Ci = 31 \text{ k}\Omega$			5	s
Oscillator stability	Δf	V <sub>DD</sub> = 2.95 to 3.05 V				3	ppm
Oscillator startup voltage	V <sub>STT</sub>	Tstt ≤ 5 s	Crystal oscillator specifications			2.4	V
Oscillator hold voltage	V <sub>HOLD</sub>		Crystal: 38 or 65 kHz	2.2		6.0	<u> </u>
Oscillator startup time	T <sub>STT</sub>	V <sub>DD</sub> = 2.4 V	XCg = 12 pF, Cl ≤ 31 kΩ			5	8
Oscillator startup voltage	V <sub>STT</sub>  _	Tstt ≤ 30 ms	CF oscillator specifications			2.2	٧
Oscillator hold voltage	VHOLD		With a 455-kHz CF element used	2.1		6.0	V
Oscillator startup time	IT <sub>STT</sub> l	V <sub>DD</sub> = 2.2 V	Ccg = Ccd = 220 pF			. 30	ms
Oscillator startup voltage	VstT	Tstt ≤ 30 ms	CF oscillator specifications			2.5	V.
Oscillator hold voltage	V <sub>HOLD</sub>		With a 1-MHz CF element used Ccg = Ccd = 100 pF	2.4		6.0	<u> </u>
Oscillator startup time	T <sub>STT</sub>	V <sub>DD</sub> = 2.5 V	- 100 μs			30	ms
Oscillator startup voltage	V <sub>STT</sub>	Tstt ≤ 30 ms	CF oscillator specifications			2.8	V
Oscillator hold voltage	V <sub>HOLD</sub> I		With a 4-MHz CF element used	2.7		6.0	V
Oscillator startup time	ΙΤ <sub>STT</sub> Ι	V <sub>DD</sub> = 2.8 V	Cog = Cod = 33 pF			30	ms
Oscillator correction capacitance	Cd	V <sub>DD</sub> = 3.0 V, XTOUT (t	ouilt in)		20	1	pF

## Continued from preceding page.

Parameter	Symbol	Conditions and applicable also		Ratings		l dan la
Parameter	Symbol	Conditions and applicable pins	min	typ	max	Unit
	R <sub>IN</sub> 1 A	V <sub>IN</sub> = 0.2 V <sub>DD</sub> , Low level hold transistor*	30	120	500	kΩ
	R <sub>IN</sub> 1 B	V <sub>IN</sub> = V <sub>OD</sub> , Pull-down resistor*	10	50	200	kΩ
	R <sub>IN</sub> 1 C	V <sub>IN</sub> = 0.8 V <sub>DD</sub> , High level hold transistor*	30	120	500	kΩ
	R <sub>IN</sub> 1 D	V <sub>IN</sub> = V <sub>SS</sub> , Pull-up resistor*	10	50	200	kΩ
Input resistance	R <sub>IN</sub> 2 A	V <sub>IN</sub> = 0.2 V <sub>DD</sub> , INT pin low level hold translator	30	120	500	kΩ
mpat redictation	R <sub>IN</sub> 2 B	V <sub>IN</sub> = V <sub>DD</sub> , tNT pin pull-down resistor	100	500	2000	kΩ
	R <sub>IN</sub> 2 C	$V_{IN} = 0.8 V_{DD}$ , INT pin high level hold transistor	30	120	500	kΩ
	R <sub>IN</sub> 2 D	V <sub>IN</sub> = V <sub>SS</sub> , INT pin pull-up resistor	100	500	2000	kΩ
	R <sub>IN</sub> 3	V <sub>IN</sub> = V <sub>DD</sub> , RES pin pull-down resistor	10	30	50	kΩ
	R <sub>IN</sub> 4	V <sub>IN</sub> = V <sub>SS</sub> , RES pin pull-up resistor	10	30	50	kΩ
	R <sub>IN</sub> 5	V <sub>IN</sub> = V <sub>DD</sub> , TST pin pull-down resistor	10	30	50	kΩ
High-level output voltage	· V <sub>OH</sub> 1	I <sub>OH</sub> = -5.0 mA, N1 to 4	V <sub>DD</sub> - 0.5			V
Low-level output voltage	V <sub>OL</sub> 1	I <sub>OL</sub> = 5.0 mA, N1 to 4			0.5	V
High-level output voltage	V <sub>OH</sub> 2	I <sub>OH</sub> = -1.0 mA, K1 to 4, P1 to 4, M1 to 4, SO1 to 4 (With the K, P, M, and SO ports in output mode)	V <sub>DD</sub> - 0.5			٧
Low-level output voltage	V <sub>OL</sub> 2	I <sub>OL</sub> = 2.0 mA, K1 to 4, P1 to 4, M1 to 4, SO1 to 4 (With the K, P, M, and SO ports in output mode)			0.5	٧
Output off leakage current	I OFF	V <sub>OH</sub> = 10.5 V, N1 to 4 (Open specifications)			1.0	μA
Segment Port Output Impedances						<del></del>
[CMOS output port mode]						
High-level output voltage	V <sub>OH</sub> 3	I <sub>OH</sub> = -500 μA, Seg 1 to 23	V <sub>DD</sub> - 0.5	*****		٧
Low-level output voltage	V <sub>OL</sub> 3	I <sub>OL</sub> = 500 μA, Seg 1 to 23			0.5	٧
[P-channel open-drain output port i	mode]		<u>, , , , , , , , , , , , , , , , , , , </u>			
High-level output voltage	V <sub>OH</sub> 3	I <sub>OH</sub> = -500 μA, Seg 1 to 23	V <sub>DD</sub> - 0.5			V
Output off leakage current	OFF	V <sub>OL</sub> = V <sub>SS</sub> , Seg 1 to 23		-	1.0	μΑ
[N-channel open-drain output port	mode]		•			
Low-level output voltage	V <sub>OL</sub> 3	I <sub>OL</sub> = 500 μA, Seg 1 to 23			0.5	٧
Output off leakage current	li OFF	V <sub>OH</sub> = V <sub>DD</sub> , Seg 1 to 23			1.0	μΑ
[Static drive]		<u> </u>				
High-level output voltage	V <sub>OH</sub> 4	I <sub>OH</sub> = -40 μA, Seg 1 to 23	V <sub>DD</sub> - 0.2			V
Low-level output voltage	V <sub>OL</sub> 4	I <sub>OL</sub> = 40 μA, Seg 1 to 23	-		0.2	٧
High-level output voltage	V <sub>OH</sub> 5	I <sub>OH</sub> = -400 μA, COM1	V <sub>DD</sub> - 0.2			V
Low-level output voltage	V <sub>OL</sub> 5	I <sub>OL</sub> = 400 μA, COM1			0.2	٧
[1/2 bias drive]	• • •	<u> </u>	<u>'</u>		<u> </u>	L
High-level output voltage	V <sub>OH</sub> 4	I <sub>OH</sub> = -40 μA, Seg 1 to 23	V <sub>DD</sub> - 0.2			V
Low-level output voltage	V <sub>OL</sub> 4	I <sub>OL</sub> = 40 μA, Seg 1 to 23			0.2	٧
High-level output voltage	V <sub>OH</sub> 5	I <sub>OH</sub> = -400 μA, COM1 to 4	V <sub>DO</sub> - 0.2			V
Output middle-level voltage	V <sub>OM</sub>	I <sub>OH</sub> = -400 μA, COM1 to 4	V <sub>DD</sub> /2 - 0.2		V <sub>DD</sub> /2 + 0.2	٧
Output middle-level voitage	VOM .	I <sub>OL</sub> = 400 μA, COM1 to 4	V <sub>D0</sub> /2 - 0.2		V <sub>DD</sub> /2 + 0.2	V
Low-level output voltage	V <sub>OL</sub> 5	I <sub>OL</sub> = 400 μA, COM1 to 4			0.2	٧
[1/3 bias drive]	-		·			
High-level output voltage	V <sub>OH</sub> 4	I <sub>OH</sub> =40 μA, Seg1 to 23	V <sub>DD</sub> - 0.2			V
Output middle-level voltage	V <sub>OM</sub> 1-1	I <sub>OH</sub> = -40 μA, Seg1 to 23	2V <sub>DD</sub> /3 - 0.2		2V <sub>DD</sub> /3 + 0.2	٧
Carpet Inicate-1046t Actade	V <sub>OM</sub> 1-2	I <sub>OL</sub> = 40 μA, Seg1 to 23	2V <sub>DD</sub> /3 - 0.2		2V <sub>DD</sub> /3 + 0.2	٧
Low-level output voltage	V <sub>OL</sub> 4	I <sub>OL</sub> = 40 μA, Seg 1 to 23			0.2	٧
High-level output voltage	V <sub>OH</sub> 6	I <sub>OH</sub> = -400 μA, COM1 to 4	V <sub>DD</sub> - 0.2			V
Output middle-level voltage	V <sub>OM</sub> 2-1	I <sub>OH</sub> = -400 μA, COM1 to 4	2V <sub>DD</sub> /3 - 0.2		2V <sub>DO</sub> /3 + 0.2	٧
oathat undais-iskei koitads	V <sub>OM</sub> 2-2	I <sub>OL</sub> = 400 μA, COM1 to 4	V <sub>DD</sub> /3 - 0.2		V <sub>DD</sub> /3 + 0.2	V
Low-level output voltage	V <sub>OL</sub> 6	I <sub>OL</sub> = 400 μA, COM1 to 4			0.2	v

#### Continued from preceding page.

		Conditions and applicable pins		Ratings			Link
Parameter	Symbol Conditions and applicable pins		min	typ	max	Unit	
Out-labeled a surrent	ILEK1	V <sub>DD</sub> = 6.0 V, Ta = 25°C			0.2	1.0	μA
Supply leakage current	ILEK2	V <sub>DD</sub> = 6.0 V, Ta = 50°C			1.0	5.0	μA
Input leakage current	i OFF	V <sub>IN</sub> = V <sub>DD</sub> V <sub>DD</sub> = 3.0 to 4, SO1	V, S1 to 4, K1 to 4, P1 to 4, M1 to 4, INT, RES K, P, M, and SO ports in input			1.0	μΑ
	1011	V <sub>IN</sub> = V <sub>SS</sub> mode and selected for	with the open specifications r the INT and RES pins.)	-1.0			μA
Output voltage 2	V <sub>DD</sub> 1-2	V <sub>DD</sub> = 5.0 V, C1 = C2 = fopg = 32.768 kHz	0.1 μF, V <sub>DD</sub> 1 = V <sub>DD</sub> 2, 1/2Bias,	2.4	2.5	2.6	٧
	V <sub>DD</sub> 1-3	V <sub>DD</sub> = 5.0 V, C1 = C2 =	V <sub>DD</sub> = 5.0 V, C1 = C2 = 0.1 μF			1.8	٧
Output voltage 3	V <sub>DD</sub> 2-3	1/3 bias, fopg = 32.768	kHz	3.1	3.33	3.5	٧
	(I <sub>DD</sub>  1-1	V <sub>DD</sub> = 5.0 V, Ta = 25°C			45.0	60.0	μA
Current drain 1	I <sub>DD</sub>  1-2	V <sub>DD</sub> = 5.0 V, Ta = 50°C	Cg = 11 pF, Cl = 31 kΩ Hait mode, LCD = 1/3blas			65	μА
	1 <sub>DD</sub>  2-1	V <sub>DD</sub> = 5.0 V, Ta = 25°C	CF oscillator specifications CF: 455 kHz		450	600	μΑ
Current drain 2	100 2-2	V <sub>DD</sub> = 5.0 V, Ta = 50°C	Ccg = Ccd = 220 pF Halt mode, LCD = 1/3 bias			650	μΑ
	I <sub>DD</sub>  3-1		CF oscillator specifications CF: 4000 kHz		500	700	μA
Current drain 3	I <sub>DD</sub>  3-2	V <sub>DD</sub> = 5.0 V, Ta = 50°C	Ccg = Ccd = 33 pF Halt mode, LCD = 1/3 bias			800	μА
	I <sub>OD</sub>  4-1	V <sub>DD</sub> = 5.0 V, Ta = 25°C	10,:0000 1012		800	1000	μA
Current drain 4	I <sub>DD</sub> 4-2	V <sub>DD</sub> = 5.0 V, Ta = 50°C	Ccg =. Ccd = 33 pF Halt mode, LCD = 1/3 blas			1150	μА
Oscillator correction capacitance	Cd	V <sub>DD</sub> = 5.0 V, XTOUT (b	uilt in)		20		ρF

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